

ABSTRACT

An exemplary solution-processed thin film transistor formation method of the invention forms conductive solution-processed thin film material contacts, semiconductor solution-processed thin film material active regions, and dielectric solution-processed thin film material isolations in a sequence and organization to form a solution-processed thin film structure capable of transistor operation. During or after the formation of the transistor structure, laser ablation is applied to one or more of the conductive solution-processed thin film material contacts, the semiconductor solution-processed thin film material active regions and the dielectric solution-processed thin film material isolations to pattern or complete patterning of a material being selectively ablated.